IN THE SPECIFICATION:

Please replace the paragraph at page 2, lns. 5-22 with the following amended paragraph:

With respect to Group II-VI compound semiconductors represented by ZnSe, except minor examples of MgTe, ZnTe, and so forth, there exists no metal having a sufficiently large work function as its p-type electrode. Therefore, for ohmic contact formation between a p-type semiconductor and an electrode, there have been various improvements in using a contact layer. As described in Journal of Crystal Growth, vol. 214/215 (2000), pp. 1064-1070 / K. ~~Kitamura~~ Katayama et al., it is the present state that use is mainly made of two techniques, i.e. forming a ZnTe/ZnSe inclined structure or forming ZnTe/ZnSe MQW (multiple quantum well) structure, and arranging a metal (electrode metal) such as AU thereon. This is because, since p-ZnTe is capable of doping up to a hole concentration of $10^{19}cm^{-3}$ (Journal of Crystal Growth, vol. 138 (1994), pp. 677-685 / A. Ishibashi et al., Applied Physics Letters, vol. 61 (1992), pp. 3160-3162 / Y. Fan et al.) so as to be easily reduced in resistance, it is possible to form an ohmic contact using Au or the like.

Please replace the paragraph at page 3, lns. 3-11 with the following amended paragraph:

Further, an electrode using p-ZnTe is not necessarily stable. As described in Journal of Crystal Growth, vol. 214/215 (2000), pp. 1064-1070 / K. ~~Kitamura~~ Katayama et al., it is known that a contact resistance increases due to long-term operation of a semiconductor element to finally cause breakage thereof. It is considered that this is because crystal defect occurs at a ZnTe/ZnSe interface due to Joule heat generation caused by the contact resistance present from the beginning.